

R D Vispute

List of Publications by Year in descending order

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59
papers

3,656
citations

279487

23
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182168

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docs citations

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times ranked

3166
citing authors

#	ARTICLE	IF	CITATIONS
1	Homo- and hetero-epitaxial growth of hexagonal and cubic Mg _x Zn _{1-x} O alloy thin films by pulsed laser deposition technique. Journal Physics D: Applied Physics, 2007, 40, 4887-4895.	1.3	16
2	Oxygen-dependent phosphorus networking in ZnO thin films grown by low temperature rf sputtering. Journal of Applied Physics, 2007, 101, 063538.	1.1	8
3	Niobium doped TiO ₂ : Intrinsic transparent metallic anatase versus highly resistive rutile phase. Journal of Applied Physics, 2007, 102, .	1.1	144
4	Advances in pulsed-laser-deposited AlN thin films for high-temperature capping, device passivation, and piezoelectric-based RF MEMS/NEMS resonator applications. Journal of Electronic Materials, 2006, 35, 777-794.	1.0	19
5	Structural and Optical Studies of Multi Shape ZnO Nanostructures Grown by Direct Vapor Phase Technique. Materials Research Society Symposia Proceedings, 2006, 957, 1.	0.1	1
6	Microstructural study of epitaxial Zn _{1-x} Mg _x O composition spreads. Journal of Applied Physics, 2005, 98, 083526.	1.1	25
7	Realization of Mg(x=0.15)Zn(1-x=0.85)O-based metal-semiconductor-metal UV detector on quartz and sapphire. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 982-985.	0.9	51
8	Effects of high-temperature anneals on 4H-SiC Implanted with Al or Al and Si. Journal of Applied Physics, 2004, 96, 5613-5618.	1.1	9
9	Electrical, CL, EPR and RBS study of annealed SiC implanted with Al or Al and C. Physica Status Solidi A, 2004, 201, 486-496.	1.7	12
10	Compositionally-tuned epitaxial cubic Mg _x Zn _{1-x} O on Si(100) for deep ultraviolet photodetectors. Applied Physics Letters, 2003, 82, 3424-3426.	1.5	241
11	Electrical, thermal, and microstructural characteristics of Ti/Al/Ti/Au multilayer Ohmic contacts to n-type GaN. Journal of Applied Physics, 2003, 93, 1087-1094.	1.1	132
12	Monolithic multichannel ultraviolet detector arrays and continuous phase evolution in Mg _x Zn _{1-x} O composition spreads. Journal of Applied Physics, 2003, 94, 7336-7340.	1.1	201
13	Electrical Activation Processes in Ion Implanted SiC Device Structures. AIP Conference Proceedings, 2003, , .	0.3	1
14	Realization of band gap above 5.0 eV in metastable cubic-phase Mg _x Zn _{1-x} O alloy films. Applied Physics Letters, 2002, 80, 1529-1531.	1.5	548
15	A comparison of graphite and AlN caps used for annealing ion-implanted SiC. Journal of Electronic Materials, 2002, 31, 568-575.	1.0	11
16	Stress origin and relaxation in epitaxial AlN thin films on SiC. Materials Research Society Symposia Proceedings, 2001, 696, 1.	0.1	0
17	BN protective coating for high temperature applications. Materials Research Society Symposia Proceedings, 2001, 697, 331.	0.1	1
18	Ultraviolet photoconductive detector based on epitaxial Mg _{0.34} Zn _{0.66} O thin films. Applied Physics Letters, 2001, 78, 2787-2789.	1.5	254

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19	Single Quantum Well Heterostructures of MgZnO/ZnO/MgZnO on C-Plane Sapphire. Materials Research Society Symposia Proceedings, 2000, 623, 359.	0.1	3
20	Annealing Study of Ga Implanted p-Type 6H-SiC for Ohmic Contact Metallizations. Materials Research Society Symposia Proceedings, 2000, 640, 1.	0.1	0
21	Optimization of Laser Energy Fluence in Pulsed Laser Deposition of ZnO on Al ₂ O ₃ (0001). Materials Research Society Symposia Proceedings, 2000, 648, 1.	0.1	0
22	Room Temperature ZnO/Zn _{0.8} Mg _{0.2} O Resonant Tunneling Devices For Microwave Applications. Materials Research Society Symposia Proceedings, 2000, 656, 141.	0.1	1
23	The properties of annealed AlN films deposited by pulsed laser deposition. Journal of Electronic Materials, 2000, 29, 262-267.	1.0	13
24	Al, B, and Ga ion-implantation doping of SiC. Journal of Electronic Materials, 2000, 29, 1340-1345.	1.0	31
25	An SEM Investigation of Annealing Encapsulants for SiC. Microscopy and Microanalysis, 2000, 6, 1094-1095.	0.2	0
26	Growth of large-scale GaN nanowires and tubes by direct reaction of Ga with NH ₃ . Applied Physics Letters, 2000, 77, 3731-3733.	1.5	199
27	Approaches For Reduction Of The Defect Density In Group III Nitride Based Heterostructures. Materials Research Society Symposia Proceedings, 2000, 639, 511.	0.1	1
28	Effectiveness of AlN encapsulant in annealing ion-implanted SiC. Journal of Applied Physics, 1999, 86, 746-751.	1.1	38
29	Leakage currents in high-quality pulsed-laser deposited aluminum nitride on 6H silicon carbide from 25 to 450°C. Journal of Applied Physics, 1999, 86, 4052-4054.	1.1	15
30	Pt and W ohmic contacts to p-6H-SiC by focused ion beam direct-write deposition. Journal of Electronic Materials, 1999, 28, 136-140.	1.0	15
31	Pulsed laser deposition and processing of wide band gap semiconductors and related materials. Journal of Electronic Materials, 1999, 28, 275-286.	1.0	30
32	Oxygen pressure-tuned epitaxy and optoelectronic properties of laser-deposited ZnO films on sapphire. Applied Physics Letters, 1999, 75, 3947-3949.	1.5	315
33	First Observation of Atomic Long Range Ordering in Metal-Oxide Based ZnMgO Wide Bandgap Heterostructures. Materials Research Society Symposia Proceedings, 1999, 583, 189.	0.1	1
34	Solid Phase Epitaxial Recrystallization of AlN Films on Sapphire (0001): A Novel Substrate Approach for GaN Epitaxy. Materials Research Society Symposia Proceedings, 1999, 587, 07.4.1.	0.1	1
35	Pulsed-Laser-Deposited AlN Films for High-Temperature SiC MIS Devices. Materials Research Society Symposia Proceedings, 1999, 595, 1.	0.1	2
36	Ohmic contacts to p-6H-SiC using focused ion-beam surface-modification and pulsed laser epitaxial TiN deposition. Applied Physics Letters, 1998, 73, 3545-3547.	1.5	17

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37	AlN as an encapsulate for annealing SiC. Journal of Applied Physics, 1998, 83, 8010-8015.	1.1	25
38	Heteroepitaxy of ZnO on GaN and its implications for fabrication of hybrid optoelectronic devices. Applied Physics Letters, 1998, 73, 348-350.	1.5	425
39	Growth of epitaxial GaN films by pulsed laser deposition. Applied Physics Letters, 1997, 71, 102-104.	1.5	101
40	Pulsed Laser Deposition of Gallium Nitride on Sapphire. Materials Research Society Symposia Proceedings, 1997, 468, 99.	0.1	2
41	Pulsed Laser Deposition of Highly Crystalline Gan Films on Sapphire. Materials Research Society Symposia Proceedings, 1997, 482, 410.	0.1	2
42	Heteroepitaxial Growth Of ZnO Films BY PLD. Materials Research Society Symposia Proceedings, 1997, 474, 383.	0.1	1
43	Pld Epitaxial Tin Contacts To 6H-Sic And Gan. Materials Research Society Symposia Proceedings, 1997, 483, 235.	0.1	1
44	Pld Epitaxial Tin And Pt Ohmic Metallizations To P-Type 6H-Sic Using Focused Ion Beam Surface Modification. Materials Research Society Symposia Proceedings, 1997, 483, 253.	0.1	0
45	Study of Electrical Transport Across Interfaces between Wide Gap Semiconductor and Metal Oxides. Materials Research Society Symposia Proceedings, 1997, 474, 119.	0.1	0
46	High quality crystalline ZnO buffer layers on sapphire (001) by pulsed laser deposition for III-V nitrides. Applied Physics Letters, 1997, 70, 2735-2737.	1.5	218
47	Laser processing of BN and AlN films. Journal of Electronic Materials, 1996, 25, 143-149.	1.0	19
48	Pulsed laser deposition of titanium nitride and diamond-like carbon films on polymers. Journal of Electronic Materials, 1996, 25, 151-156.	1.0	52
49	Epitaxial TiN based contacts for silicon devices. Journal of Electronic Materials, 1996, 25, 1740-1747.	1.0	6
50	LaNiO ₃ and Cu ₃ Ge contacts to YBa ₂ Cu ₃ O _{7-x} films. Journal of Electronic Materials, 1996, 25, 1760-1766.	1.0	7
51	Characterization of highly oriented (110) TiN films grown on epitaxial Ge/Si(001) heterostructures. Journal of Materials Research, 1996, 11, 399-411.	1.2	7
52	Characteristics of titanium nitride films grown by pulsed laser deposition. Journal of Materials Research, 1996, 11, 1458-1469.	1.2	90
53	Epitaxial Tin Films on Sapphire and Silicon-on-Sapphire by Pulsed Laser Deposition. Materials Research Society Symposia Proceedings, 1995, 397, 271.	0.1	1
54	High quality epitaxial aluminum nitride layers on sapphire by pulsed laser deposition. Applied Physics Letters, 1995, 67, 1549-1551.	1.5	141

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55	Misfit dislocations in low-temperature grown Ge/Si heterostructures. Philosophical Magazine A: Physics of Condensed Matter, Structure, Defects and Mechanical Properties, 1995, 71, 537-551.	0.8	25
56	Epitaxial growth of AlN thin films on silicon (111) substrates by pulsed laser deposition. Journal of Applied Physics, 1995, 77, 4724-4728.	1.1	144
57	Pulsed laser deposition and characterization of epitaxial Cu/TiN/Si(100) heterostructures. Applied Physics Letters, 1994, 65, 2565-2567.	1.5	33
58	Pulsed Laser Deposition and Characterization of Novel Cu/TiN/Si(100) Heterostructures Grown VIA Domain Epitaxy. Materials Research Society Symposia Proceedings, 1994, 355, 39.	0.1	0
59	Formation of Submicron Single Crystal Particles and Dots by Laser Ablation. Materials Research Society Symposia Proceedings, 1994, 358, 145.	0.1	0